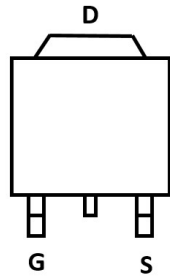
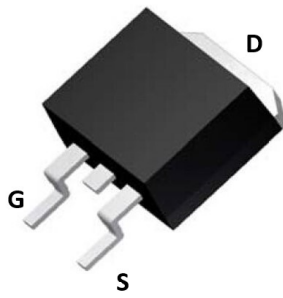
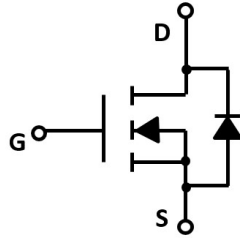


## N-Channel Enhancement Mode Field Effect Transistor



**TO-263**



### Product Summary

- $V_{DS}$  100V
- $I_D$  70A
- $R_{DS(ON)}$ ( at  $V_{GS}=10V$ )  $< 8.6$  mohm
- $R_{DS(ON)}$ ( at  $V_{GS}=6V$ )  $< 13$  mohm
- 100% UIS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Low  $R_{DS(on)}$  & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery

### Applications

- Power switching application
- Hard switched and high frequency circuits
- UPS

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	100	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current <sup>A</sup> (Package Limited)	$T_C=25^\circ C$	$I_D$	70	A
	$T_C=100^\circ C$		44	
Pulsed Drain Current <sup>B</sup>		$I_{DM}$	280	A
Avalanche energy <sup>C</sup>		$E_{AS}$	200	mJ
Total Power Dissipation <sup>D</sup>	$T_C=25^\circ C$	$P_D$	125	W
	$T_C=100^\circ C$		50	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Thermal resistance

		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>E</sup>	$t \leq 10S$	$R_{\theta JA}$	12	15	$^\circ C/W$
Thermal Resistance Junction-to-Ambient <sup>E</sup>	Steady-State		50	60	
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.8	1.0	

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB70G10B	F2	YJB70G10B	800	/	8000	13" reel



# YJB70G10B

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	100			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	2	2.8	4	V
Static Drain-Source On-Resistance	R <sub>Ds(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =20A		7.2	8.6	mΩ
		V <sub>GS</sub> = 6V, I <sub>D</sub> =20A		10	13	mΩ
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =20A, V <sub>GS</sub> =0V			1.3	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				70	A
Gate resistance	R <sub>G</sub>	f= 1 MHz, Open drain		0.68		Ω
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHZ		2270		pF
Output Capacitance	C <sub>oss</sub>			797		
Reverse Transfer Capacitance	C <sub>rss</sub>			36		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =25A		32		nC
Gate-Source Charge	Q <sub>gs</sub>			11.1		
Gate-Drain Charge	Q <sub>gd</sub>			4.78		
Reverse Recovery Chrage	Q <sub>rr</sub>	I <sub>F</sub> =20A, di/dt=100A/us		84		ns
Reverse Recovery Time	t <sub>rr</sub>			51.5		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =50V, I <sub>D</sub> =25A R <sub>GEN</sub> =2.2Ω		51		ns
Turn-on Rise Time	t <sub>r</sub>			14.4		
Turn-off Delay Time	t <sub>D(off)</sub>			69.2		
Turn-off fall Time	t <sub>f</sub>			20.6		

- A. The maximum current rating is package limited.  
 B. Repetitive rating; pulse width limited by max. junction temperature.  
 C. V<sub>DD</sub>=50V, R<sub>G</sub>=25Ω, L=0.5mH, starting T<sub>J</sub>=25 °C.  
 D. Pd is based on max. junction temperature, using junction-case thermal resistance.  
 E. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub> =25°C. The Power dissipation PDSM is based on R<sub>θJA</sub> t<sub>S</sub> ≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



# YJB70G10B

## ■ Typical Performance Characteristics

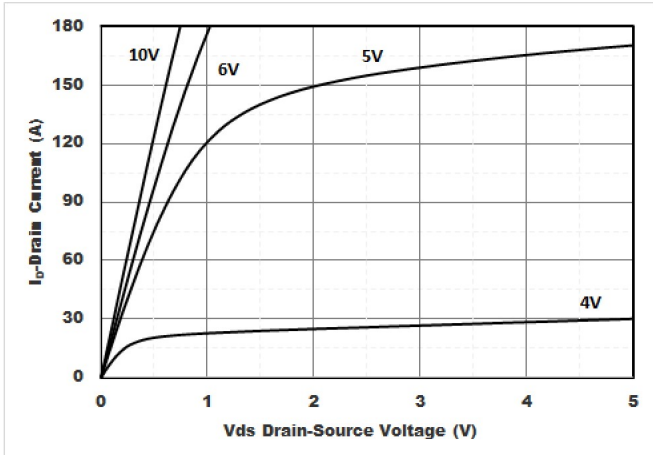


Figure1. Output Characteristics

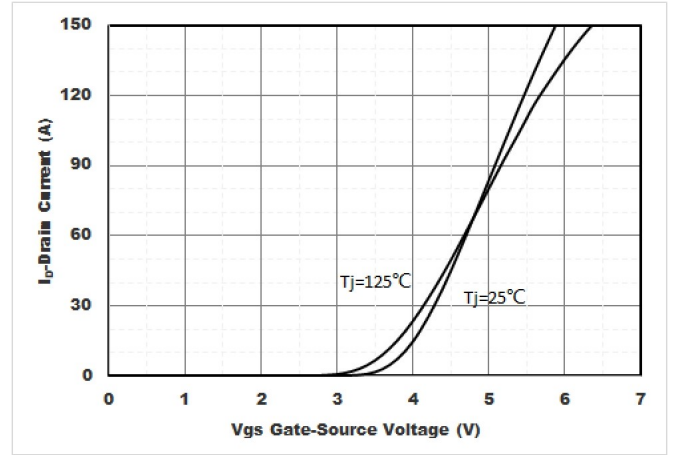


Figure2. Transfer Characteristics

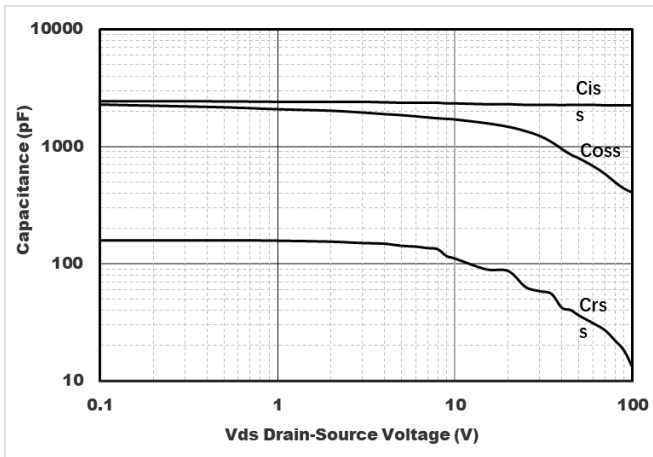


Figure3. Capacitance Characteristics

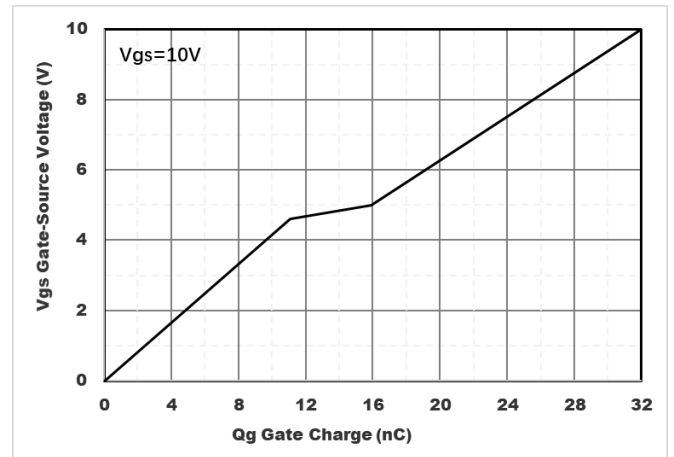


Figure4. Gate Charge

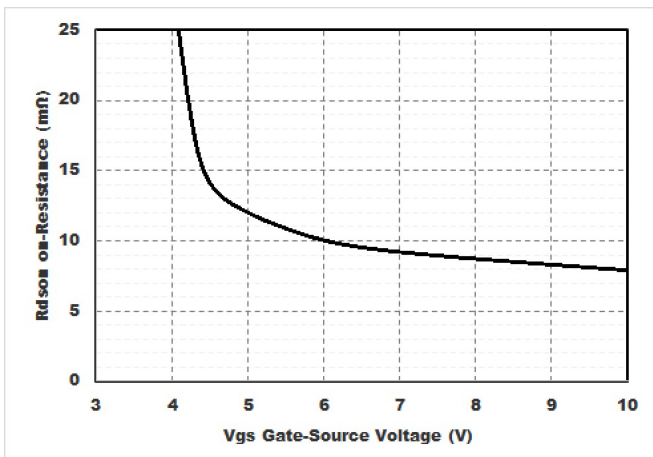


Figure5. : On-Resistance vs. Drain Current and Gate Voltage

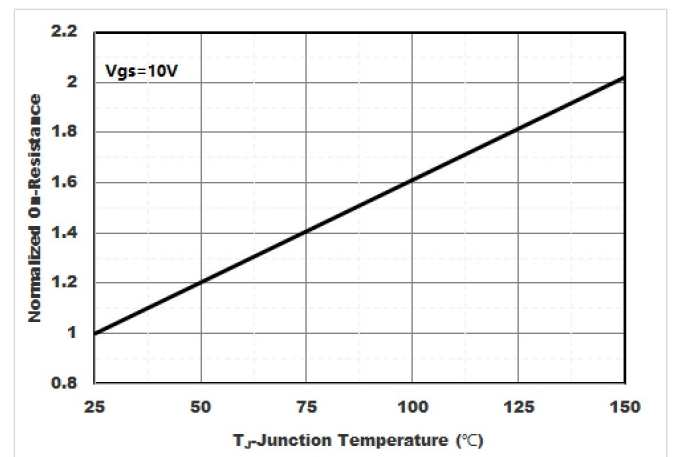


Figure6. Normalized On-Resistance



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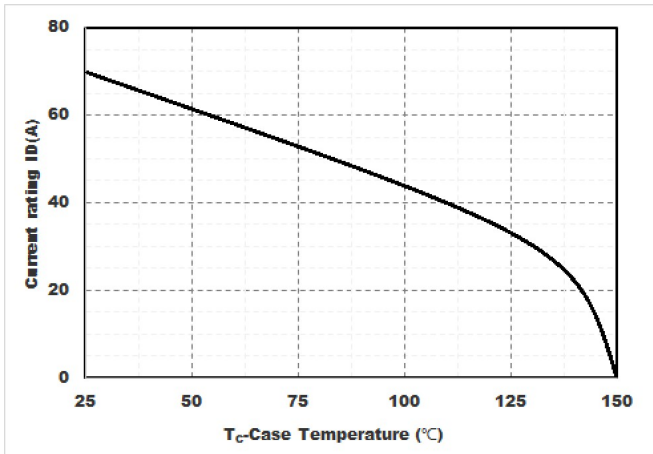


Figure7. Drain current

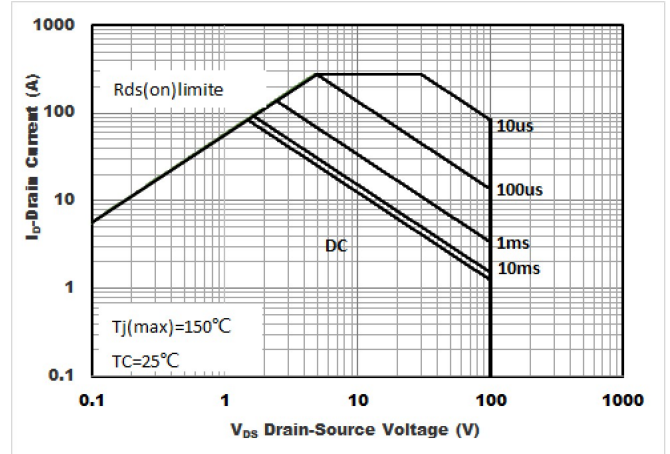


Figure8.Safe Operation Area

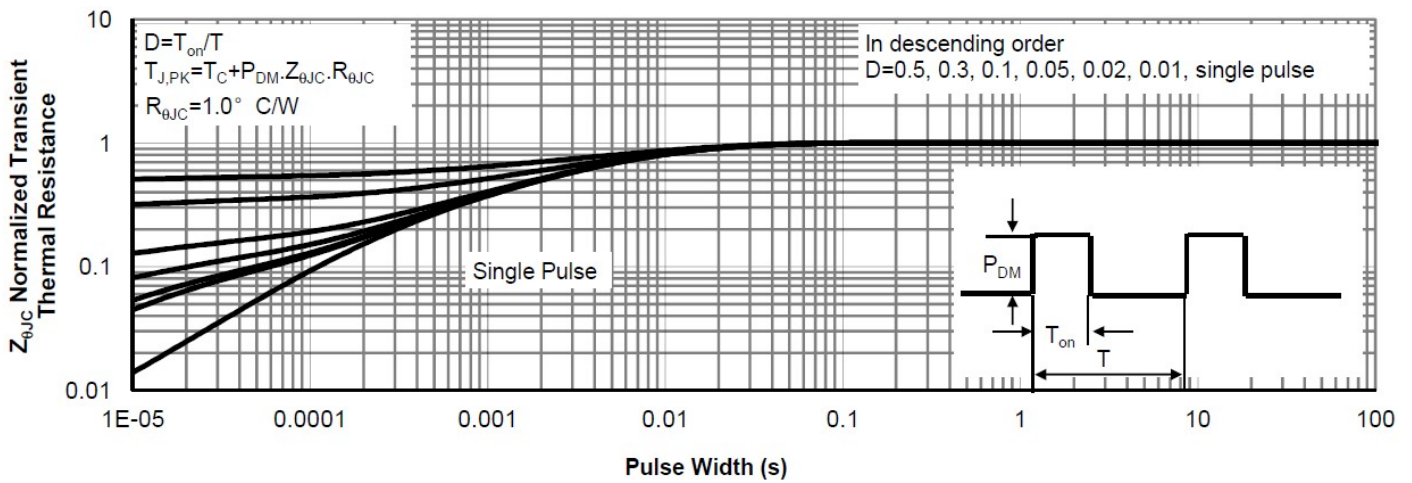
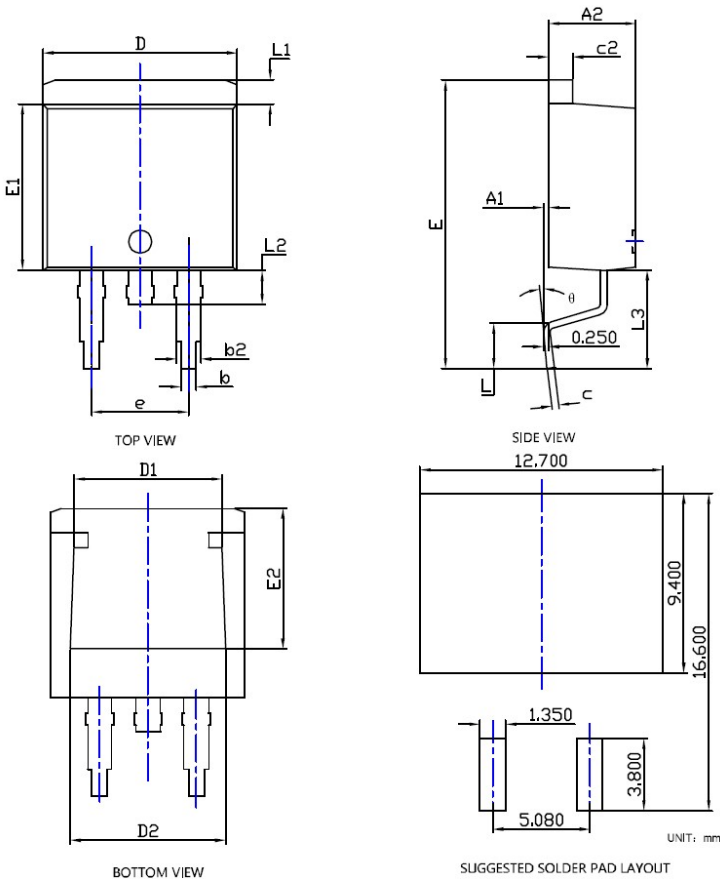


Figure9.Normalized Maximum Transient thermal impedance



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## ■ TO-263 Package information



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.010	0.000	---	0.250
A2	0.174	0.180	0.186	4.430	4.580	4.730
b	0.028	0.032	0.036	0.720	0.820	0.920
b2	0.046	0.050	0.054	1.180	1.280	1.380
c	0.013	0.015	0.018	0.330	0.390	0.450
c2	0.048	0.050	0.053	1.220	1.280	1.34
D	0.394	0.400	0.406	10.000	10.150	10.300
D1	0.295	0.307	0.319	7.500	7.800	8.100
D2	0.303	0.315	0.327	7.700	8.000	8.300
E	0.571	0.591	0.610	14.500	15.000	15.500
E1	0.337	0.341	0.348	8.550	8.700	8.850
E2	0.276	0.287	0.299	7.000	7.300	7.600
e	0.200BSC			5.080BSC		
L	0.070	---	0.110	1.790	---	2.790
L1	0.044	---	0.056	1.120	---	1.420
L2	0.030	---	0.070	0.770	---	1.770
L3	0.197REF			5.000REF		
∅	0*	---	8*	0*	---	8*

### NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



## YJB70G10B

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